

EVVOSEMI[®]

THINK CHANGE DO



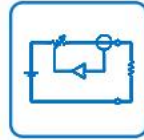
ESD



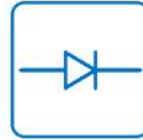
TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	BFG540
▶ Overseas	Part Number	BFG540
▶ Equivalent	Part Number	BFG540

EV is the abbreviation of name EVVO

BFG540 系列 NPN 微波低噪声晶体管

BFG540; BFG540/X(ON4832/X);BFG540/XR NPN TRANSISTOR MICROWAVE LOW NOISE AMPLIFIER NPN SILICON EPITAXIAL TRANSISTOR

1. 简述:

本芯片采用硅外延工艺制造，具有高功率增益、低噪声系数、较宽的转换频率、低漏电流、金材质引出结构，具有较高的可靠性；

✚ 主要应用于超高频微波、VHF、UHF 和 CATV 高频宽带低噪声放大器中，如数字有线电视电视机顶盒、卫星电视调谐器、CATV 放大器、模拟数字无绳电话、射频模块和光纤传输中的中继放大器等产品；

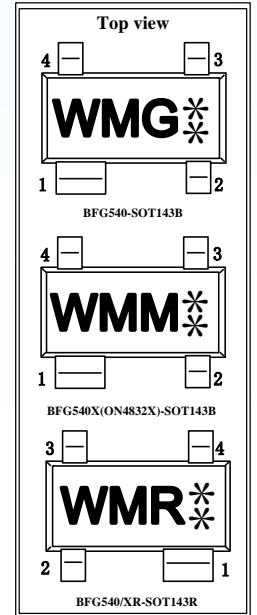
✚ 集电极-发射极击穿电压： $BV_{CEO}=15V$ ，最大集电极电流： $I_C=120mA$ ，集电极耗散功率： $P_C=400mW$ ，特征频率： $f_T=9GHz$ ；

✚ 4 引脚（宽集电极引脚与双发射极引脚）的 SOT143B 或者 SOT143R 表面贴塑封；

✚ ON4832/X 同 BFG540/X 的性能、封装、丝印等完全一样，只是标签型号不同。

2. 封装形式和引脚定义：

型号(Model)	BFG540	BFG540/X (ON4832/X)	BFG540/XR
封装形(Package)	SOT143B	SOT143B	SOT143R
本体丝印(Marking)	WMG	WMM	WMR
引脚(Pin)1	collector	collector	collector
引脚(Pin)2	base	emitter	emitter
引脚(Pin)3	emitter	base	base
引脚(Pin)4	emitter	emitter	emitter



3. 极限参数 ($T_{amb}=25^{\circ}C$) :

参数名称	符号	额定值	单位
集电极-基极击穿电压	BV_{CBO}	20	V
集电极-发射极击穿电压	BV_{CEO}	15	V
发射极-基极击穿电压	BV_{EBO}	2.5	V
集电极电流	I_C	120	mA
耗散功率	P_T	400	mW
最高结温	T_J	150	$^{\circ}C$
储存温度	T_{stg}	-65 ~ +150	$^{\circ}C$

4. 电参数及规格 ($T_{amb}=25^{\circ}C$) :

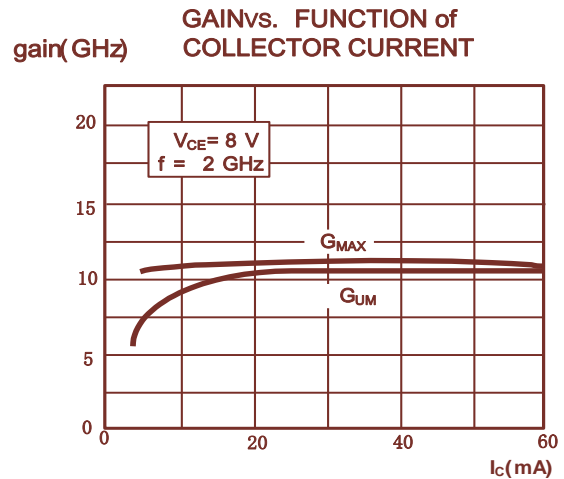
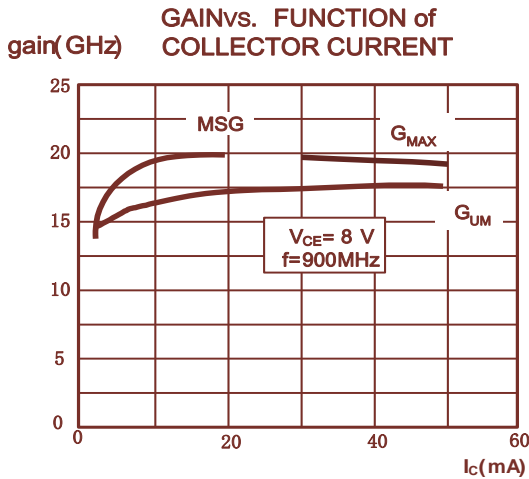
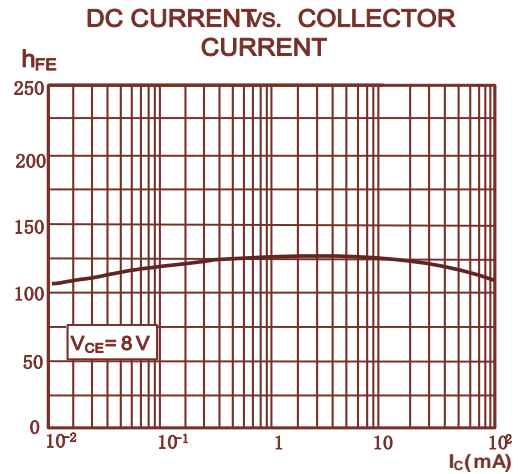
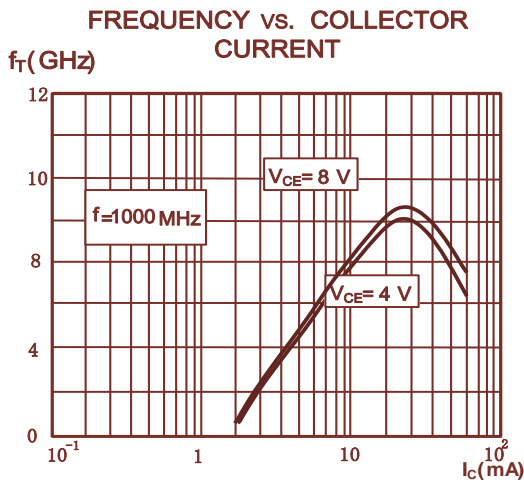
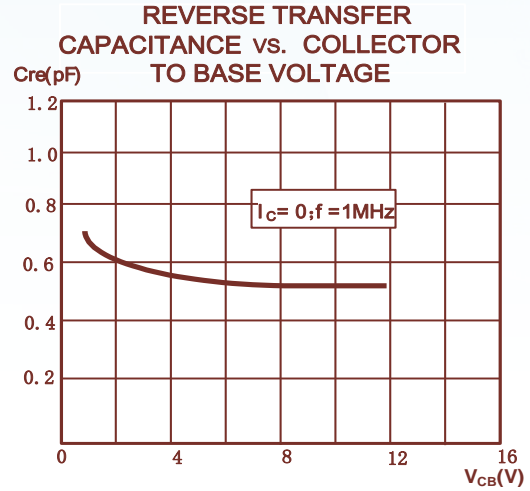
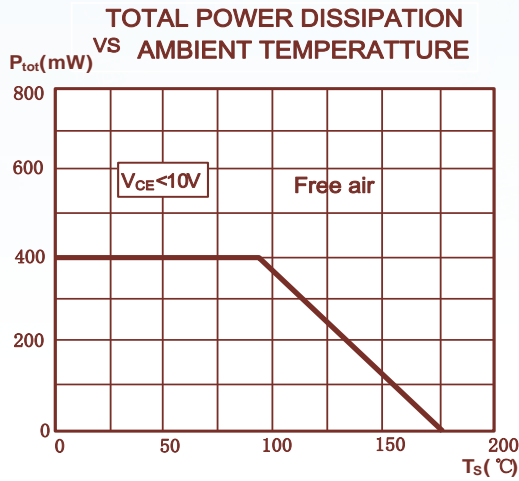
参数名称	符号	测试条件	最小值	典型值	最大值	单位
集电极截止电流	I_{CBO}	$V_{CB}=6V, I_E=0$	-	-	0.05	μA
直流电流放大系数	h_{FE}	$V_{CE}=8V, I_C=40mA$	60	120	250	
特征频率	f_T	$I_C=40mA, V_{CE}=8V, f=1MHz, T_{amb}=25^{\circ}C$	-	9	-	GHz
反馈电容	C_{re}	$I_C=I_C=0, V_{CB}=8V, f=1MHz$	-	0.5	-	pF

集电极电容	Cc	$I_E=i_e=0, V_{CB}=8V, f=1MHz$	-	0.9	-	pF
发射极电容	Ce	$I_C=i_c=0, V_{EB}=0.5V, f=1MHz$	-	2.0	-	pF
插入功率增益	$ S_{21} ^2$	$I_C=40mA, V_{CE}=8V, f=900MHz, T_{amb}=25^\circ C$	15	16	-	dB
噪声系数	NF	$V_{CE}=8V, I_C=10mA, f=900MHz, T_{amb}=25^\circ C$	-	1.3	1.8	dB
		$V_{CE}=8V, I_C=40mA, f=900MHz, T_{amb}=25^\circ C$	-	1.9	2.4	dB
		$V_{CE}=8V, I_C=10mA, f=2GHz, T_{amb}=25^\circ C$	-	2.1	-	dB
最大单边功率增益	G_{UM}^*	$I_C=40mA, V_{CE}=8V, f=900MHz, T_{amb}=25^\circ C$	-	18	-	dB
		$I_C=40mA, V_{CE}=8V, f=2GHz, T_{amb}=25^\circ C$	-	11	-	dB
第三阶截取点	ITO	$I_C=40mA, V_{CE}=8V, R_L=50\Omega, f_p=900MHz, f_q=902MHz, T_{amb}=25^\circ C$	-	34	-	dBm
输出电压	V_O	$V_O=275mV, I_C=40mA, V_{CE}=8V, Z_S=Z_L=75\Omega, f_p=795.25MHz, f_q=803.25MHz, f_r=803.25MHz, T_{amb}=25^\circ C, dim=-60dB$	-	500	-	mV
输出功率在 1dB 的增益压缩	PL1	$I_C=40mA, V_{CE}=8V, R_L=50\Omega, f=900MHz, T_{amb}=25^\circ C$	-	21	-	dBm
二阶互调失真	d_2	$V_O=275mV, I_C=40mA, V_{CE}=8V, f_p=250MHz, f_q=560MHz, T_{amb}=25^\circ C$	-	-50	-	dB

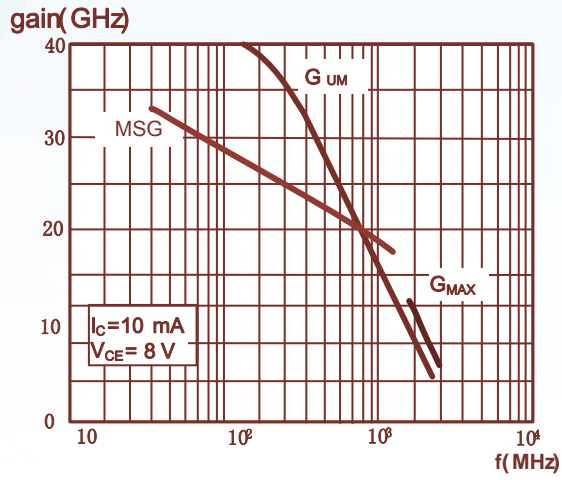
$$* G_{UM} = 10 \log \frac{|S_{21}|^2}{(1-S_{11})^2(1-S_{22})^2} dB$$

5. 典型特征曲线:

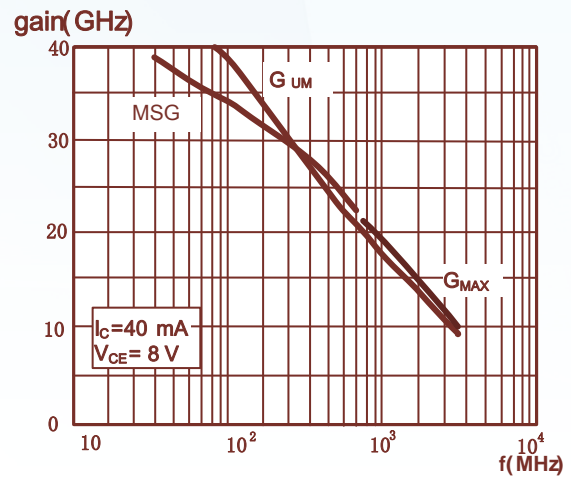
TYPICAL CHARACTERISTICS
($T_A=25^{\circ}\text{C}$, unless otherwise specified)



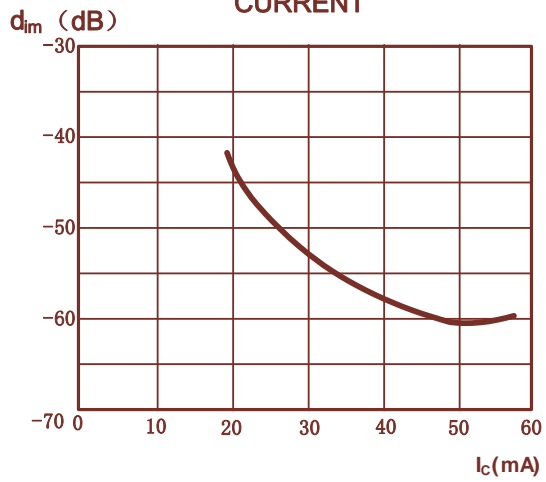
GAIN vs. FUNCTION of FREQUENCY



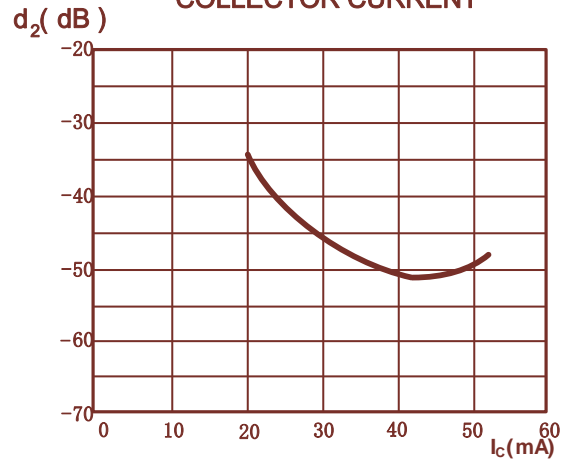
GAIN vs. FUNCTION of FREQUENCY



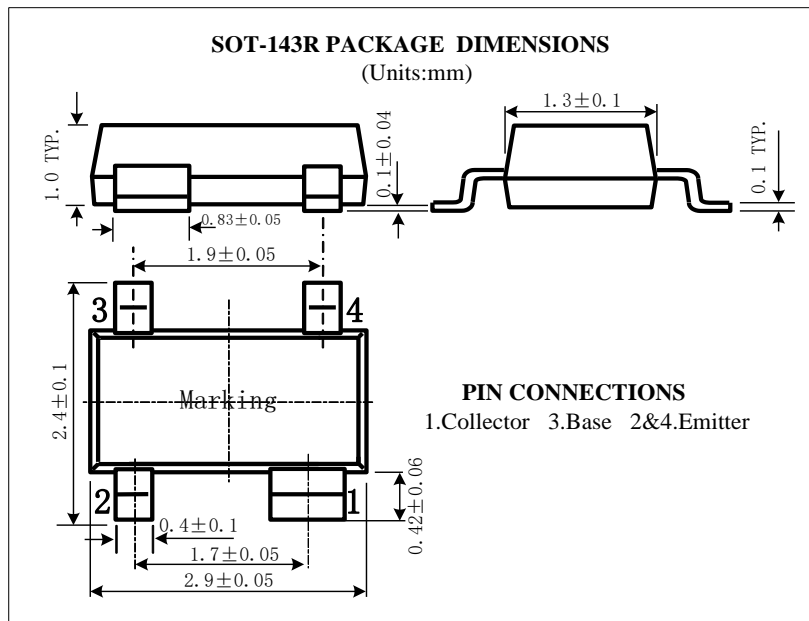
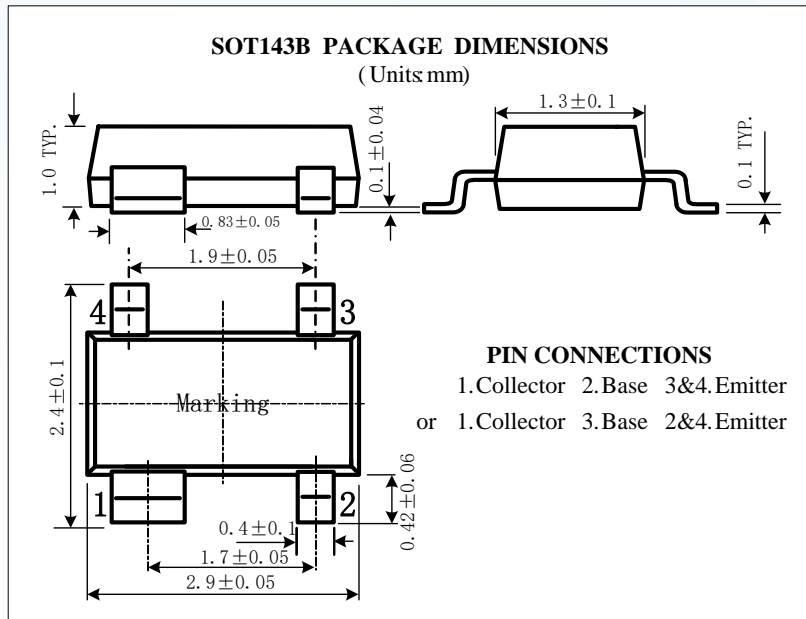
INTERMODULATION DISTORTION vs. FUNCTION of COLLECTOR CURRENT



SECOND ORDER INTERMODULATION DISTORTION vs. FUNCTION of COLLECTOR CURRENT



6. 封装尺寸示意图:



7. 包装信息:

PACKAGE INFORMATION

封装形式 Package	数量/盘 Shipping	盘/中盒 Inner Box	中盒/箱 Carton
SOT143B	3000pcs/Tape&Reel	5Tape&Reel	8-16 Inner Box
SOT143R	3000pcs/Tape&Reel	5Tape&Reel	8-16 Inner Box

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